

TO-92 Plastic-Encapsulate Transistors

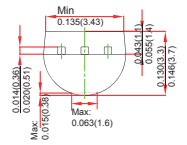
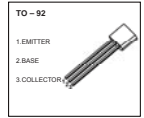
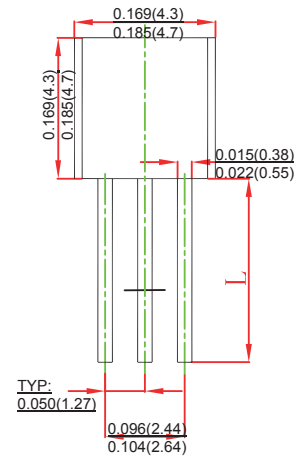
FEATURES

- Low Current
- High Voltage
- TRANSISTOR (NPN)

MECHANICAL DATA

- Case style:TO-92 molded plastic
- Mounting position:any

TO-92



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CB0}	Collector-Base Voltage	200	V
V_{CEO}	Collector-Emitter Voltage	200	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current	0.2	A
P_C	Collector Power Dissipation	625	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	200	°C/W
T_j	Junction Temperature	150	°C
T_{stg}	Storage Temperature	-55~+150	°C

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=0.1mA, I_E=0$	200			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1mA, I_B=0$	200			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=0.1mA, I_C=0$	6			V
Collector cut-off current	I_{CBO}	$V_{CB}=160V, I_E=0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=4V, I_C=0$			0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=10V, I_C=1mA$	25			
	$h_{FE(2)}$	$V_{CE}=10V, I_C=10mA$	40		200	
	$h_{FE(3)}$	$V_{CE}=10V, I_C=30mA$	50			
Collector-emitter saturation voltage	$V_{CE(sat)(1)}$	$I_C=20mA, I_B=2mA$			0.4	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=20mA, I_B=2mA$			0.9	V
Transition frequency	f_T	$V_{CE}=20V, I_C=10mA, f=100MHz$	50			MHz
Collector output capacitance	C_{ob}	$V_{CB}=20V, I_E=0, f=1MHz$			4	pF

*Pulse test: pulse width $\leq 300\mu s$, duty cycles $\leq 2.0\%$.

Marking	MPSA43
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